

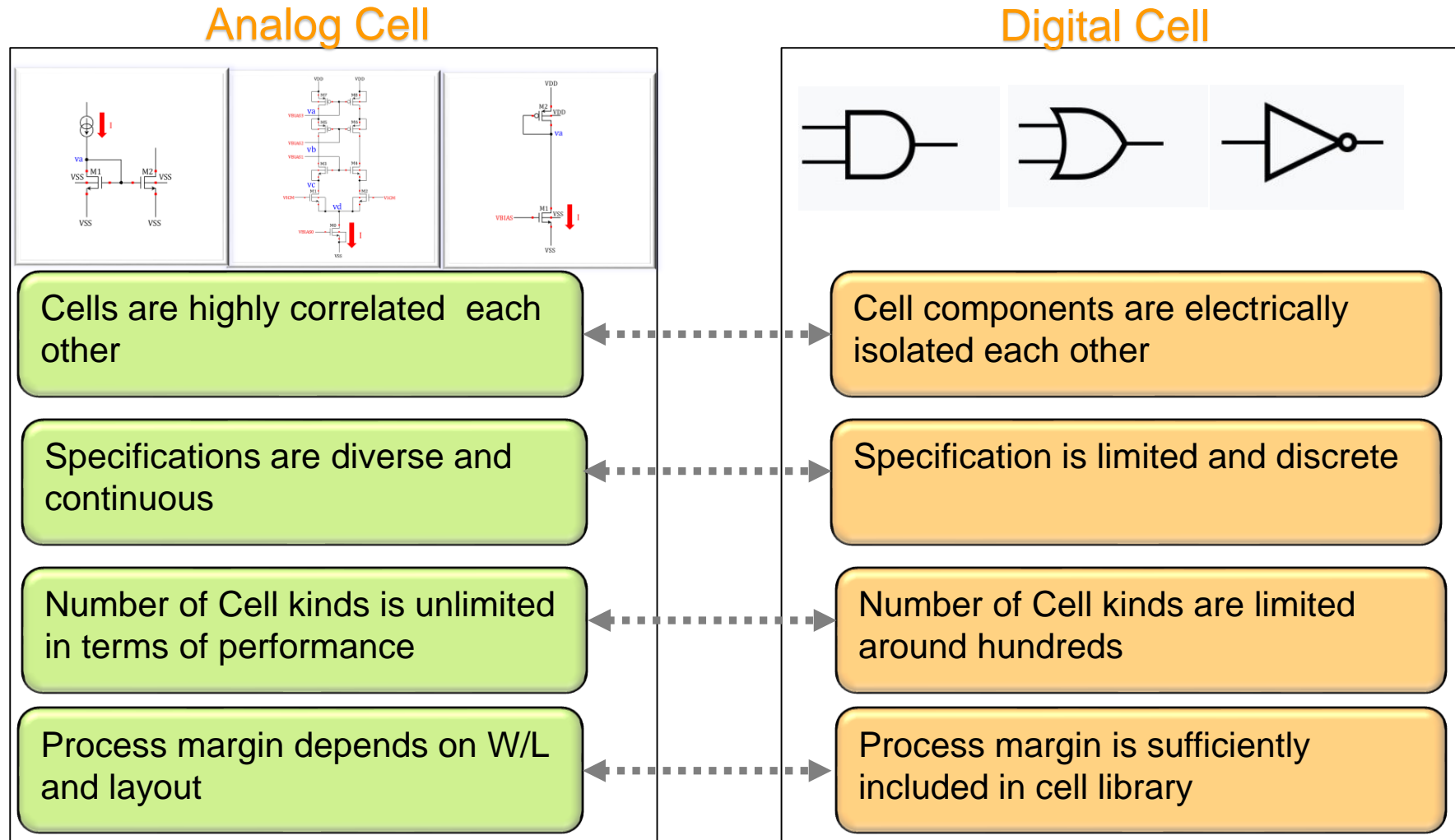
# Practical cell based analog design methodology II (AnaCell)

## Promotion of analog automatic cell generation with the designability in AnaCell

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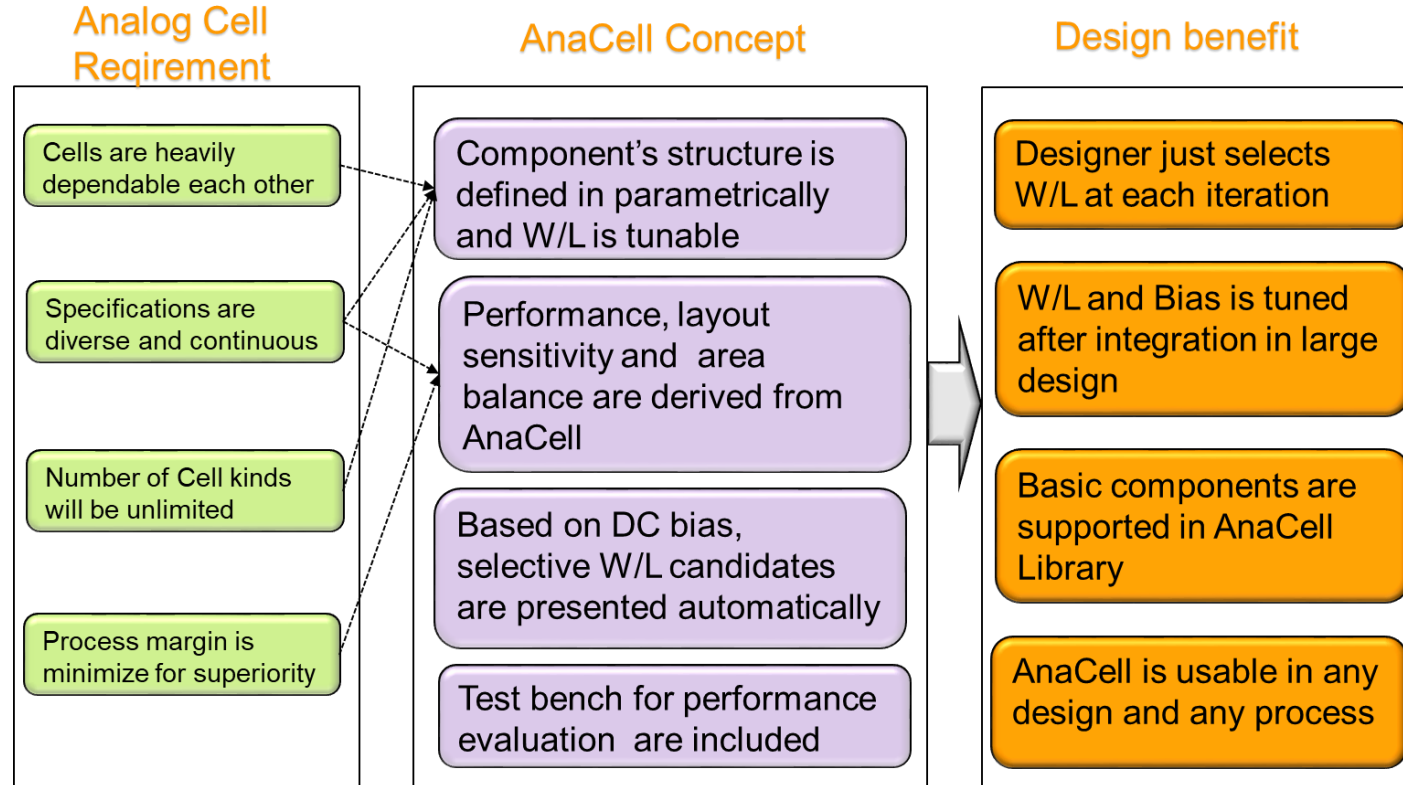
# Difficulty of analog standard cell design



Standard Cell design in Analog could not have been applied like digital design.

# Concept of AnaCell and the difficulty

AnaCell is targeting to become like the digital standard cell in Analog Design



Cell	Type	TR #	Total #
Differential Input	Current mirror	5	24
	Constant current mirror	5	
	Cascode current mirror	7	
	...	7-9	
Current Source	...	2-7	36
Amplification	...	2-4	22

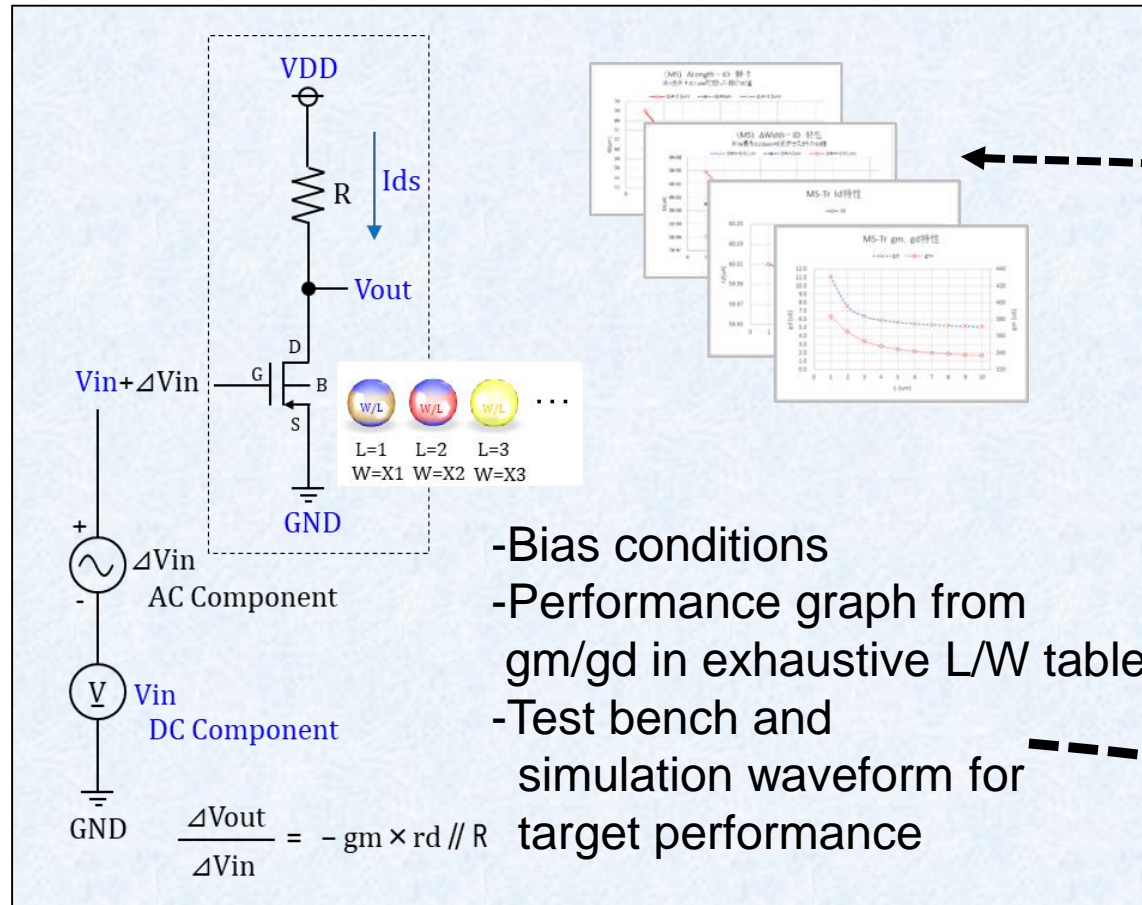
AnaCell Library

Still designer needs the iteration to find the appropriate DC bias to satisfy the various requirements in AnaCell

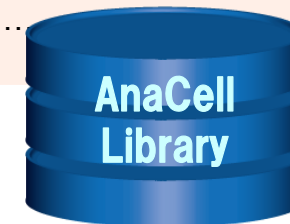
-DC bias means circuit's operating points and each Transistors'  $V_{gs}/V_{ds}/V_{bs}$  etc.

# Design methodology using AnaCell

## AnaCell



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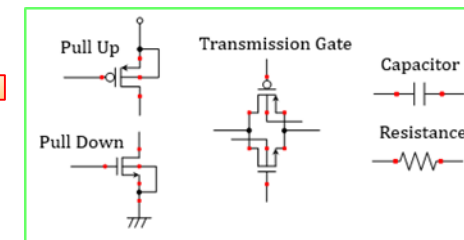
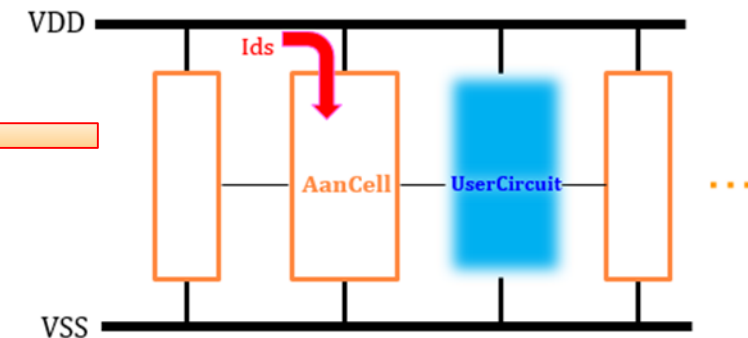
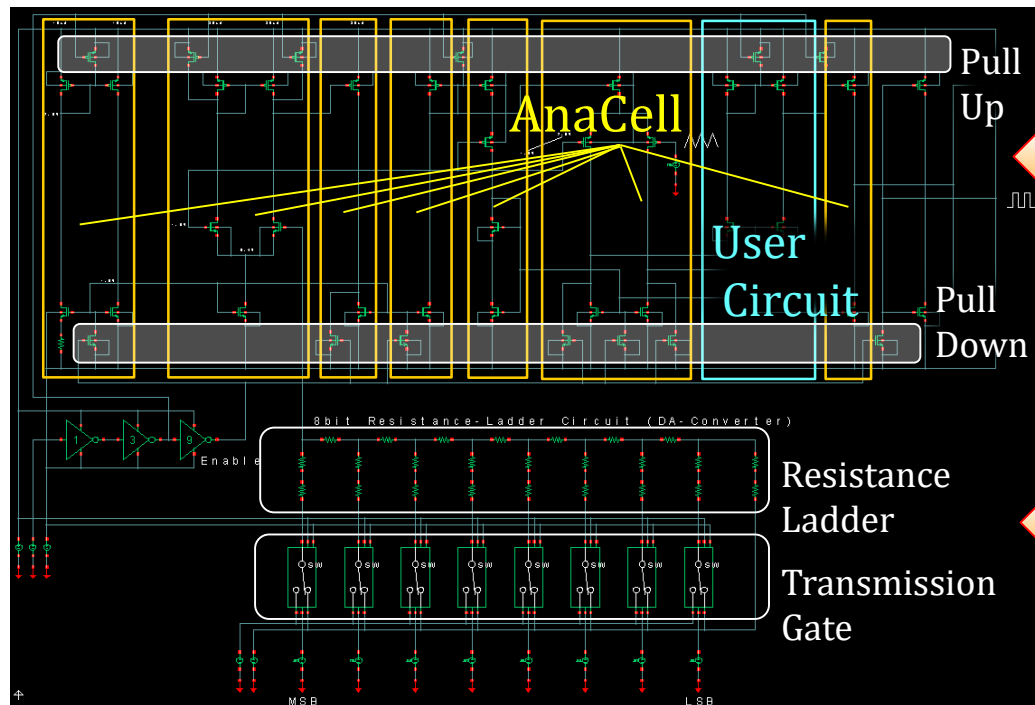


\* AnaCell is under Patent pending

Tuning each transistor's Bias and W/L in AnaCell

# AnaCell design usage

- The circuits that consist of AnaCells are suitable for Current source/OPAMP/Regulator etc.
- There is no limit in circuit size and number of AnaCells for designing
- Circuits can be designed combining AnaCells and Pull UP/Down and Gate elements

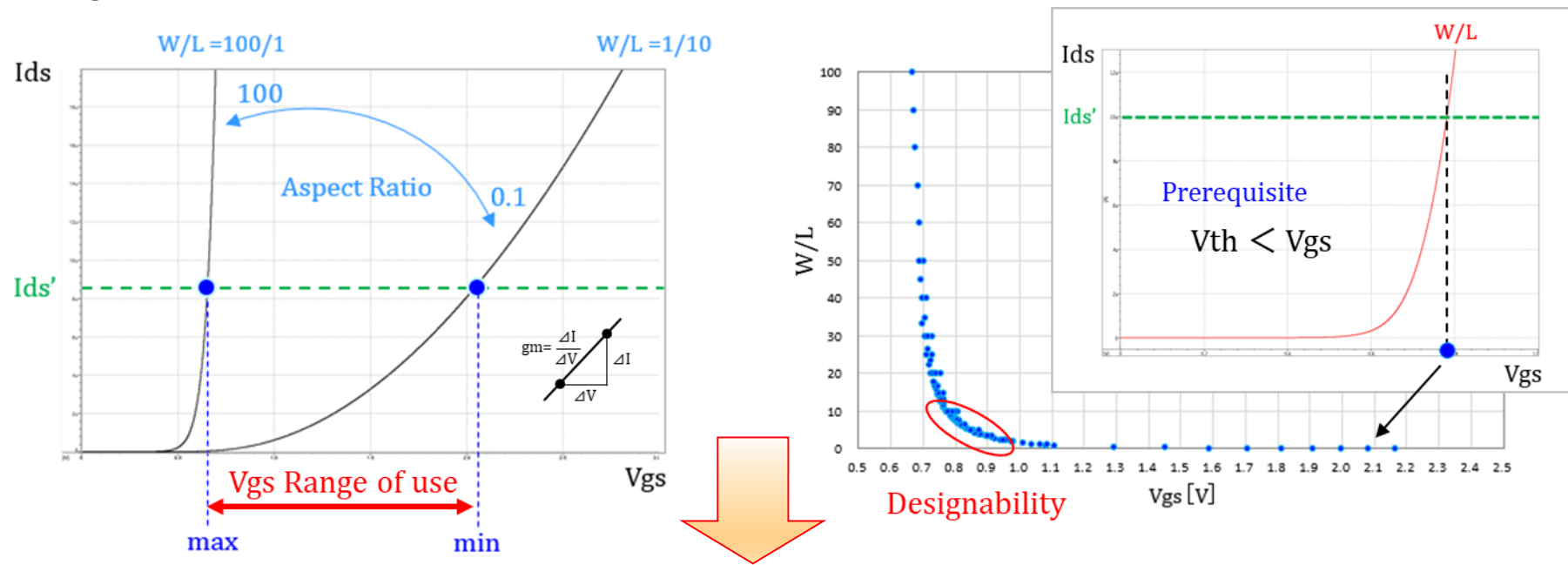


## Pulse Width Modulation Circuit

consists of AnaCell/Pullup/RESISTENCE Ladder/Transmission Gate/User Circuit

# Concern in DC bias setting and auto selection

- $V_{gs}$ ,  $V_{ds}$  has feasible range to derive a certain  $I_{ds}$  regarding  $g_m$  ( $W/L$ )
- Design space of  $W$  and  $L$  is discrete and has specific curve
- Every  $W/L$  which satisfies the target  $I_{ds}$  may be logically the candidate but in terms of designability for other metrics every  $W/L$  does not fully satisfy
- Designability: We define the designability as the freedom and allowance for design  $L/W$  for adjusting the multi objects of circuit performance.

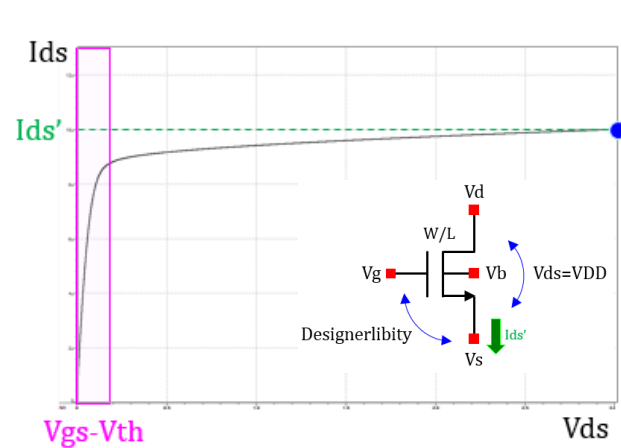


Automatic selection of the DC bias which maximizes the designability should be the best candidates for AnaCell in specific process

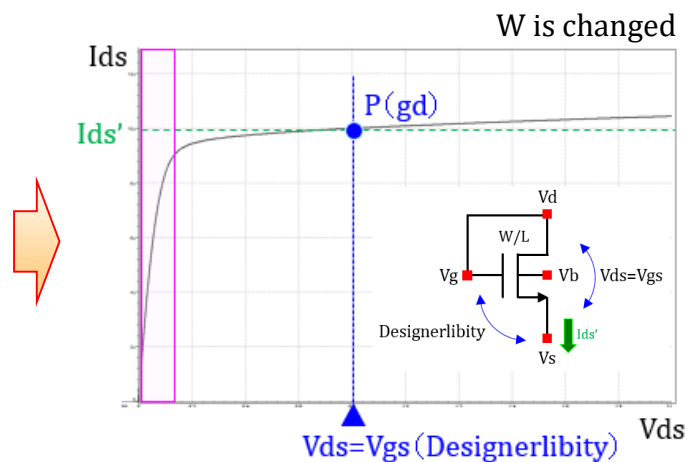
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# DC bias setting and Vds tuning 1

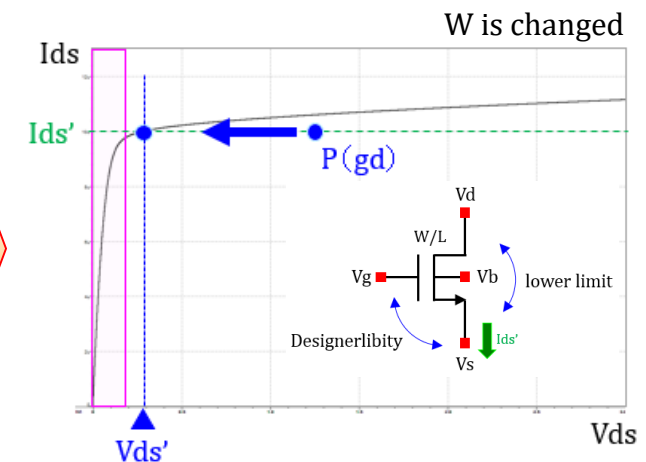
- Each transistor starts from  $V_{ds}=V_{dd}$
- Valuable  $V_{ds}$  of each transistor should be lower than  $V_{dd}$  under the condition of saturation and reasonable gd slope



Point that acquired  $V_{gs}$  (Designability)  
 $V_{ds} > V_{gs} - V_{th} \therefore$  Saturation Region



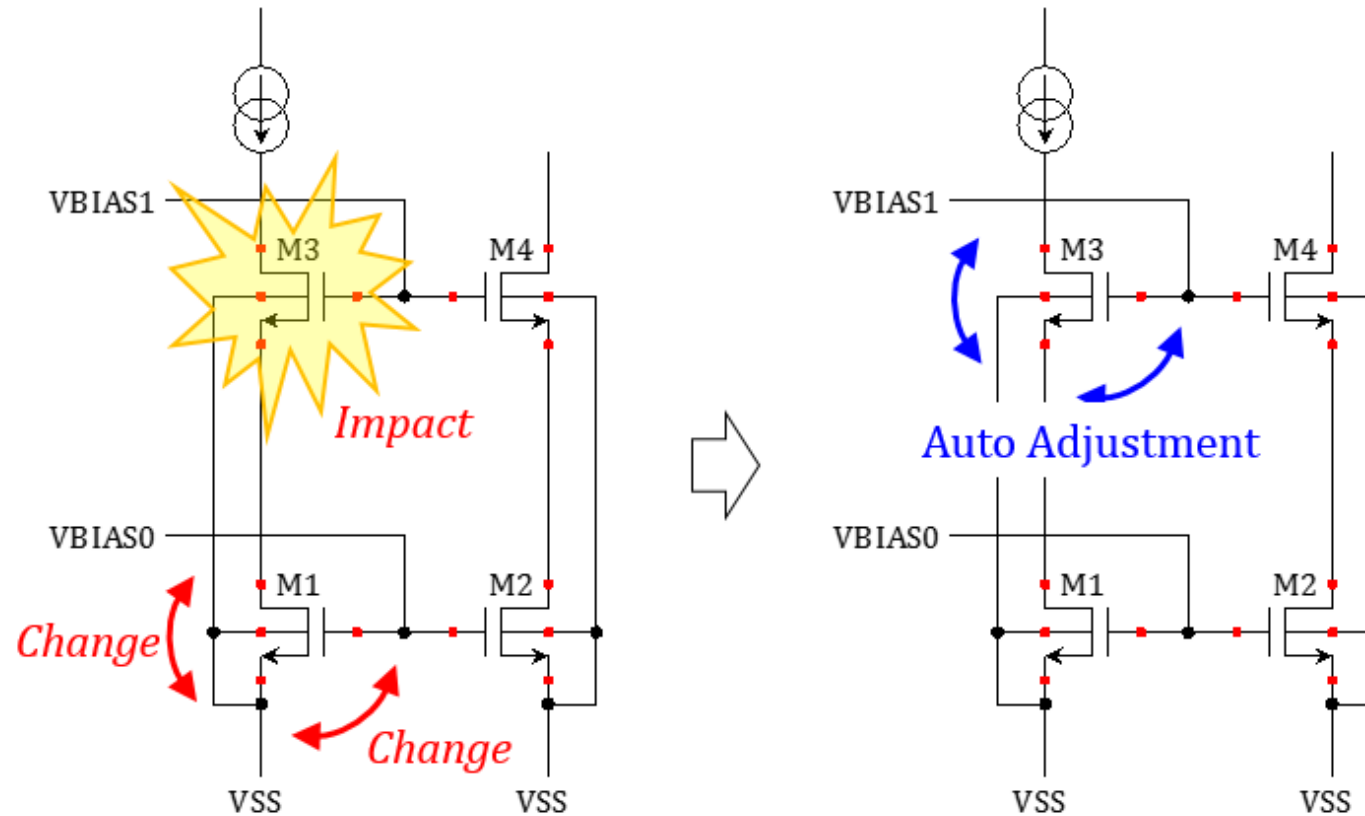
Reference Point of gd (slope)  $P(gd) = \frac{\Delta I}{\Delta V}$   
 $V_{ds}=V_{gs} \therefore$  Saturation Region



Derive the lower limit  $V_{ds}'$  based on gd  
 $V_{ds} > V_{gs} - V_{th} \therefore$  Saturation Region

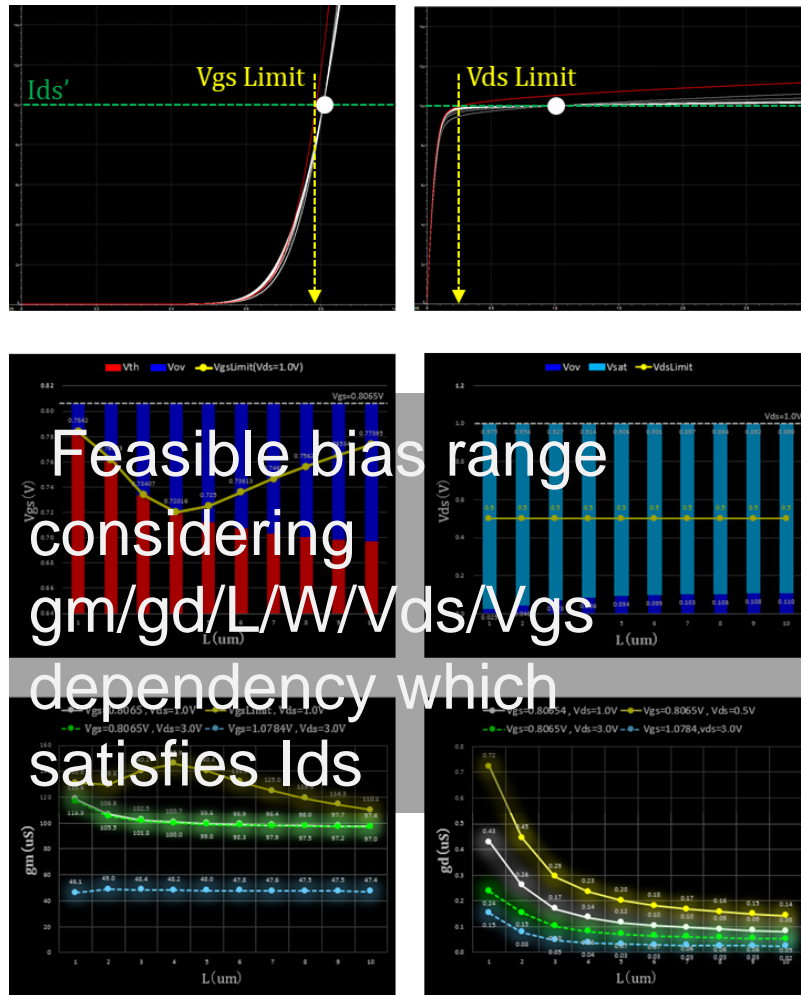
# DC bias setting and $V_{ds}$ tuning 2

- Bias of each transistor is automatically adjusted satisfying VDD-GND voltage
- This feature is also interactively usable and fast in manually adjustment without the effort of changing all transistors in AnaCell





# Design methodology using AnaCell with auto DC bias setting



Feasible bias range  
considering  
 $g_m/g_d/L/W/V_{ds}/V_{gs}$   
dependency which  
satisfies  $I_{ds}$

1. Construct Circuit by AnaCell

2. Apply Technology to AnaCell

3. Specify only supply voltage(VDD) and  $I_{ds}$  to each AnaCell and get the initial DC bias for all Transistors automatically

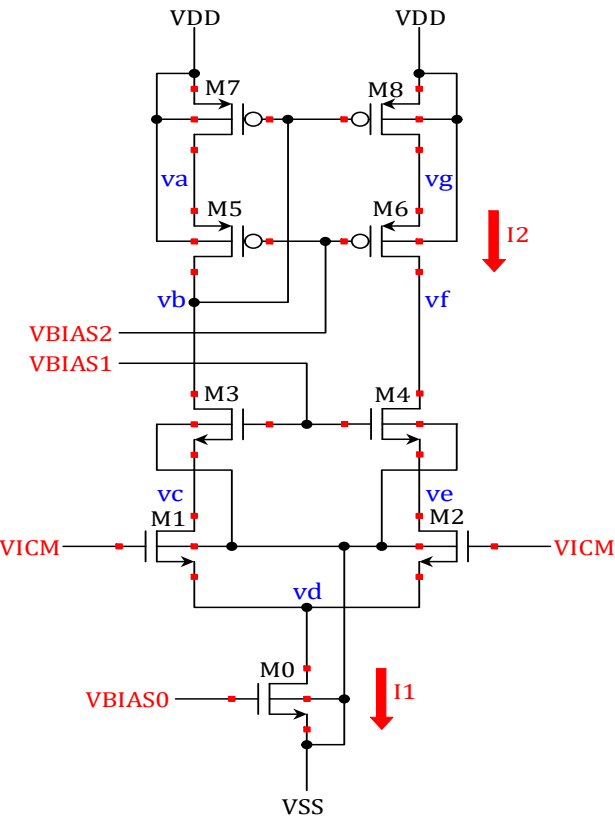
4. Select and adjust  $L$   $W$  which satisfies AnaCell requirements from candidates

5. Simulation with AC/Transient and evaluate final goal

Designer can instantly get the initial appropriate DC bias under only VDD and  $I_{ds}$  current.

# 2 Experiments in TPSCO 65nm PDK

## 1. Differential Input Circuit Single-Ended Signaling Type Telescopic Current Mirror



Input Value

VDD	3.3
VSS	0
I1	20u
I2	10u

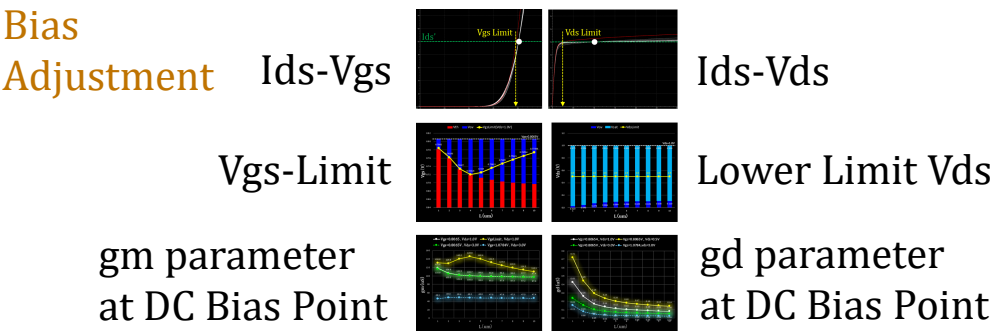
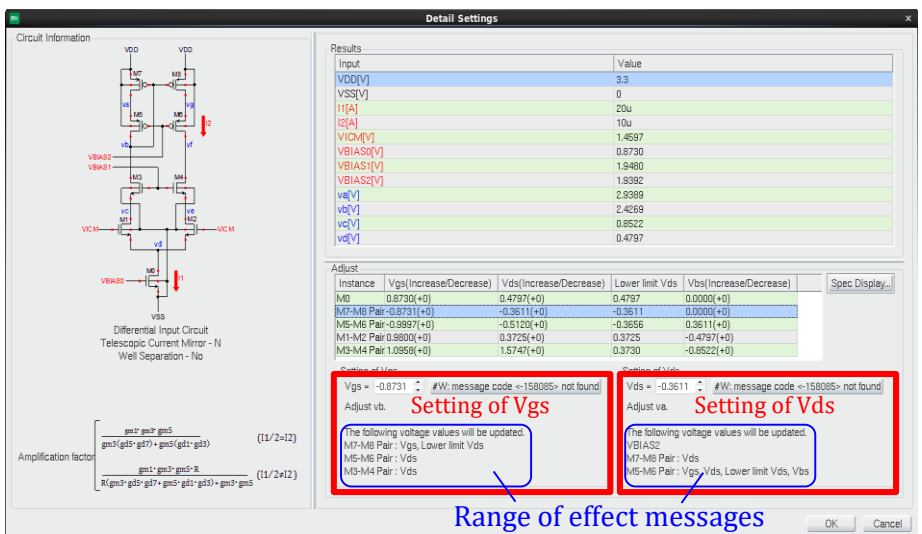
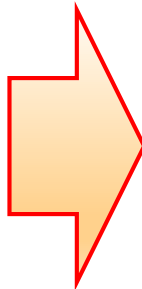
Initial Solution

VICM	1.4598
VBIAS0	0.8730
VBIAS1	1.9462
VBIAS2	1.8441
va	2.9060
vb	2.3778
vc	0.8508
vd	0.4798

Result

W/L Combination	81000
Gain	79.5 ~ 110.2dB

Initial Value

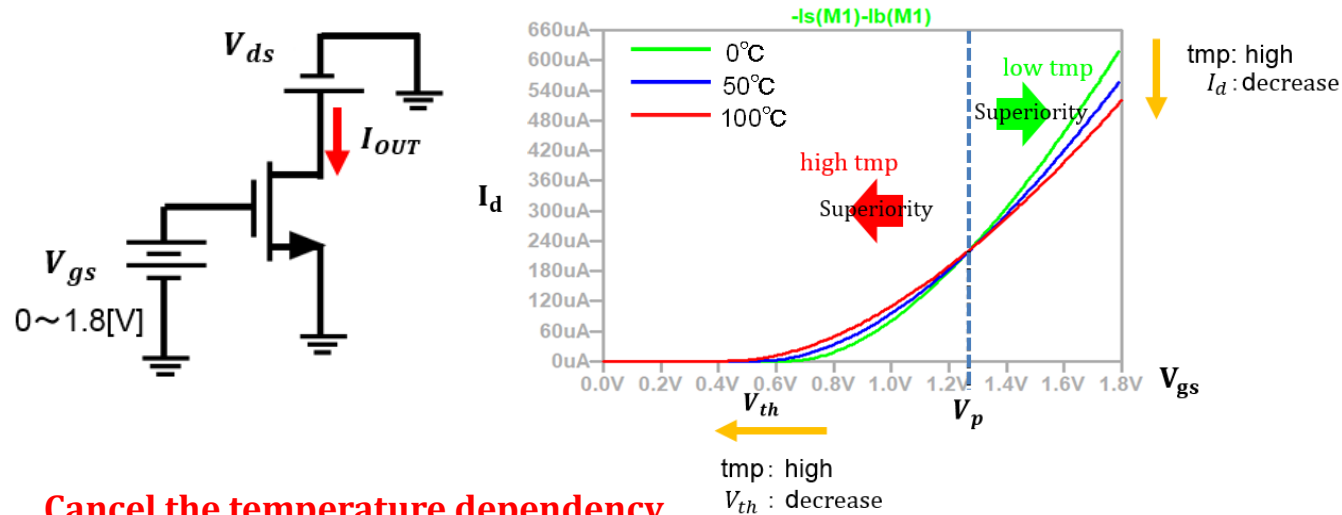


Auto Bias setting  
5minute  
(60s/1Tr searching for 10 L cases)

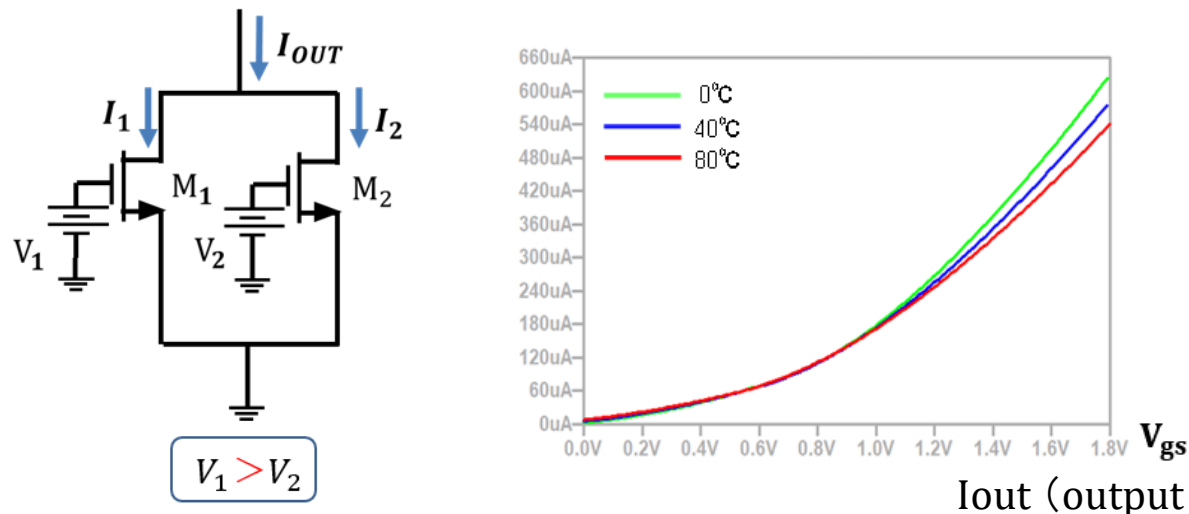
Bias Adjustment  
0 ~ 1minute  
(60s/1Tr searching)

## 2 Experiments in TPSCO 65nm PDK

### 2. MOS reference current sources that are insensitive to temperature variation

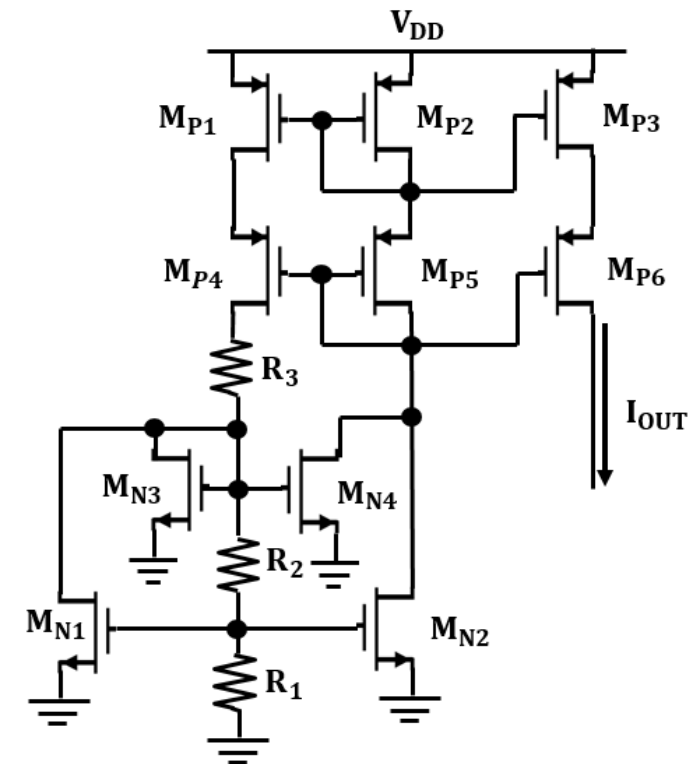


Cancel the temperature dependency



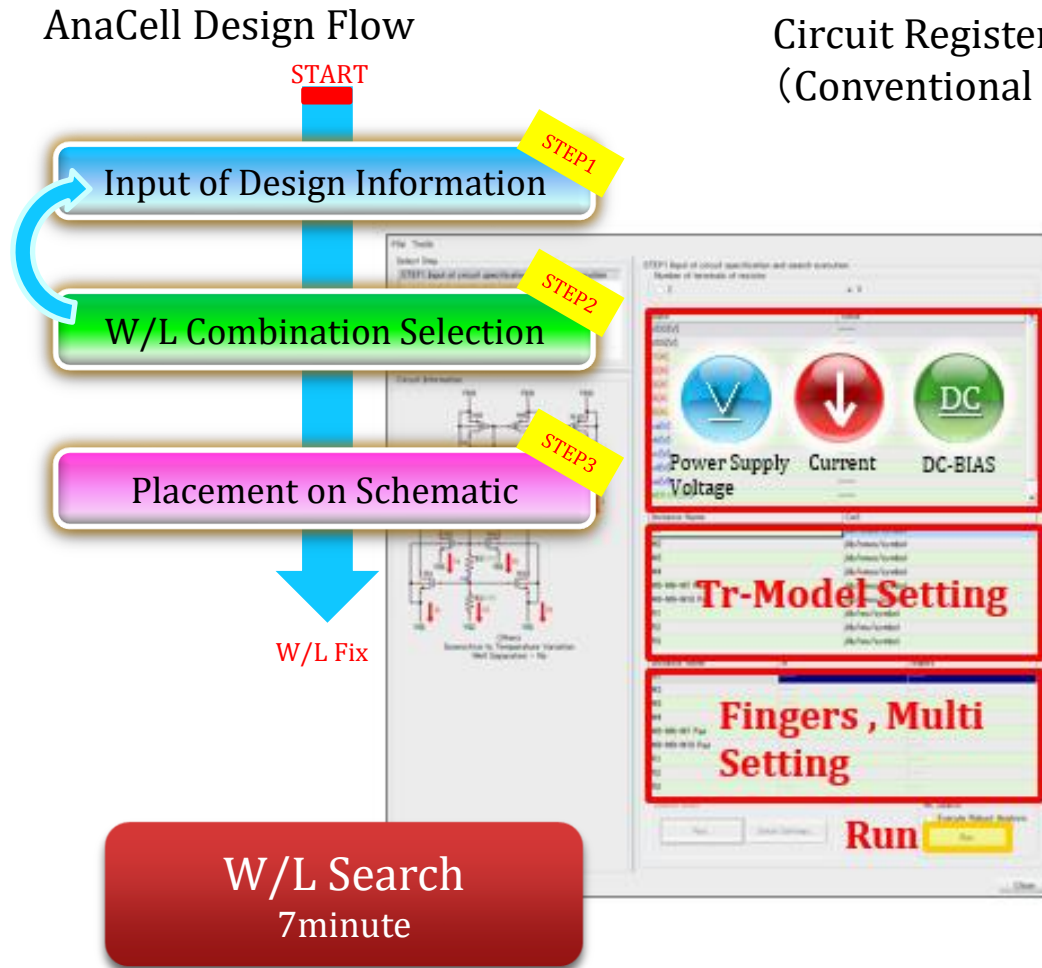
$I_{out}$  (output Current)

Circuit Registered to AnaCell



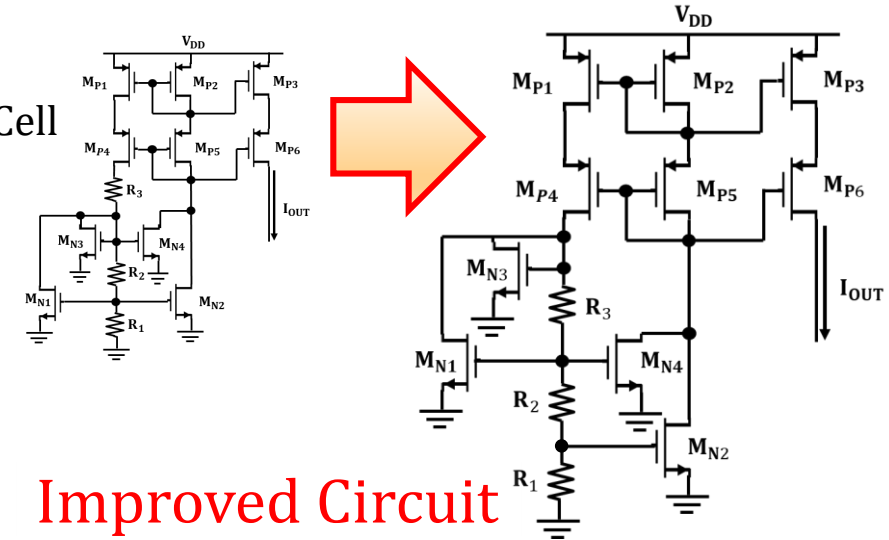
Trail performance by LW  
setting for researching

## 2 Experiments in TPSCO 65nm PDK

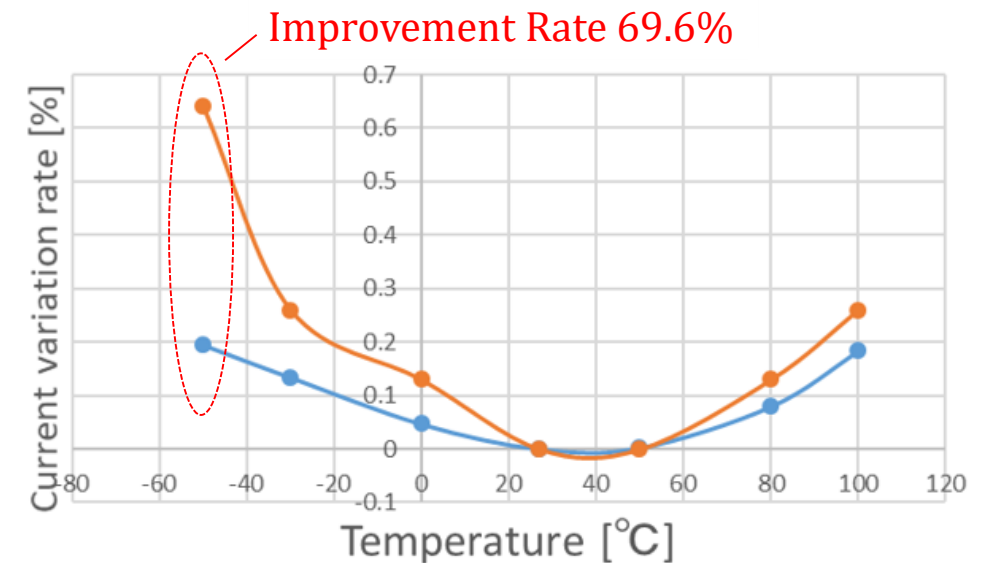


A diagram of the circuit actually converted to AnaCell

Circuit Registered to AnaCell  
(Conventional Circuit)



Improved Circuit



— Improved circuit — Conventional circuit

# Summary

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- ❑ AnaCell can be applied for cell base analog design style but previously it requires designers some efforts and skill for DC bias setting.
- ❑ We propose auto DC bias setting which considers the freedom of design allowance (we call designability) with process free and designer only needs to set VDD and Current.
- ❑ This DC bias setting data would be reuse in other AnaCell's bias if condition is same, and it improves the design time significantly.
- ❑ This will promotes to auto analog generation without loss of multi performance and designer's intent.
- ❑ This design methodology changes the design style in proven circuits and also accelerates the research for new circuit.